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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	40
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 24x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dx128vlh7

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105 • C = –40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm) • MJ = 256 MAPBGA (17 mm x 17 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MK20DN512ZVMD10

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

3.3 Definition: Attribute

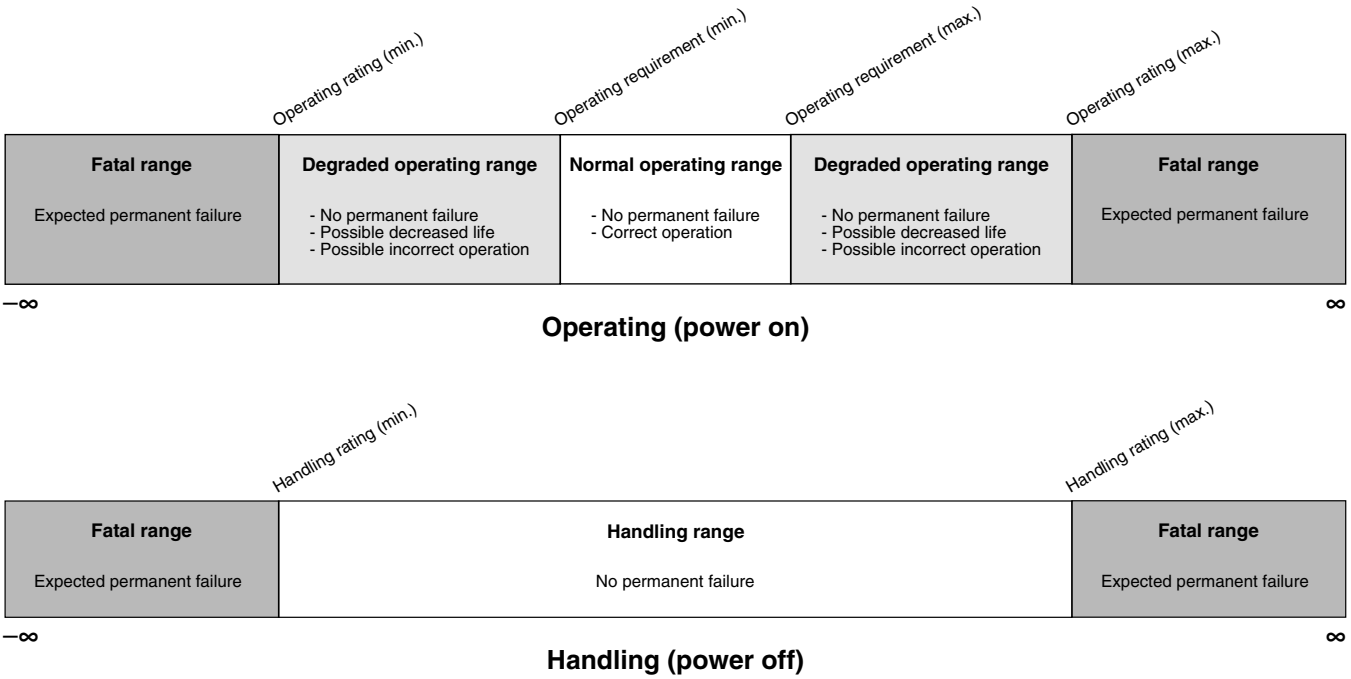
An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

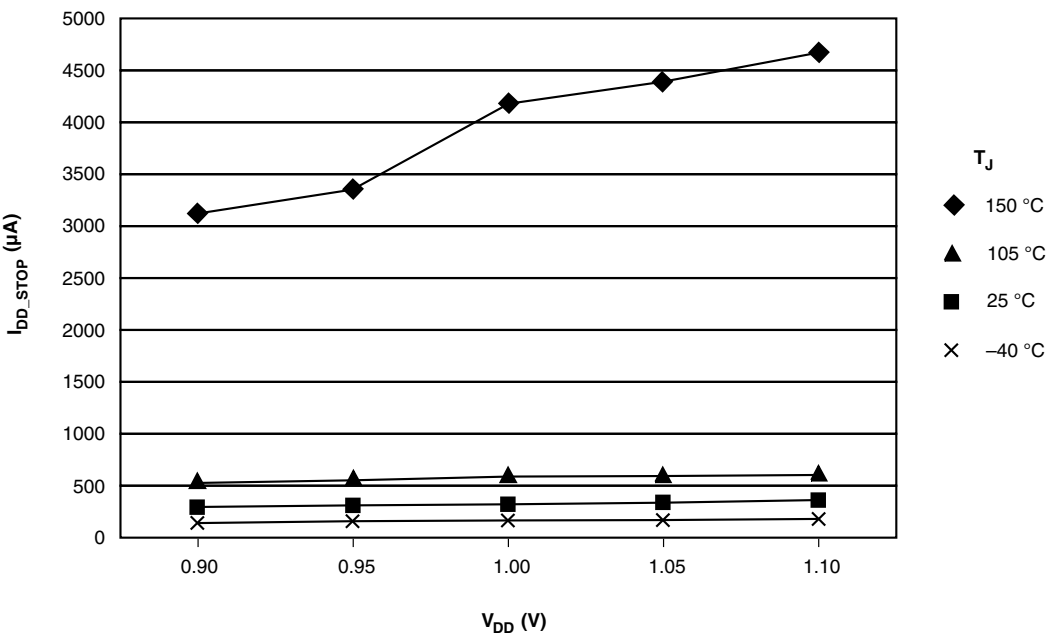
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V

Table continues on the next page...

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	µs	1
	• VLLS1 → RUN	—	112	µs	
	• VLLS2 → RUN	—	74	µs	
	• VLLS3 → RUN	—	73	µs	
	• LLS → RUN	—	5.9	µs	
	• VLPS → RUN	—	5.8	µs	
	• STOP → RUN	—	4.2	µs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					2
	• @ 1.8V	—	21.5	25	mA	
	• @ 3.0V	—	21.5	30	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3, 4
	• @ 1.8V	—	31	34	mA	
	• @ 3.0V					
	• @ 25°C	—	31	34	mA	
	• @ 125°C	—	32	39	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	12.5	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	7.2	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	0.996	—	mA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.46	—	mA	7

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers					10
	• @ 1.8V					
	• @ –40 to 25°C	—	0.57	0.67	µA	
	• @ 70°C	—	0.90	1.2	µA	
	• @ 105°C	—	2.4	3.5	µA	
	• @ 3.0V					
	• @ –40 to 25°C	—	0.67	0.94	µA	
	• @ 70°C	—	1.0	1.4	µA	
	• @ 105°C	—	2.7	3.9	µA	

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEE mode. All peripheral clocks disabled.
3. 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEE mode. All peripheral clocks enabled.
4. Max values are measured with CPU executing DSP instructions.
5. 25MHz core, system, bus and flash clock. MCG configured for FEI mode.
6. 4 MHz core and system clock, 4 MHz and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core and system clock, 4 MHz and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core and system clock, 4 MHz and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Data reflects devices with 128 KB of RAM. For devices with 64 KB of RAM, power consumption is reduced by 2 µA.
10. Includes 32kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode for 50 MHz and lower frequencies. MCG in FEE mode at greater than 50 MHz frequencies.
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

Table 9. General switching specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	16	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select ($\overline{\text{EZP\_CS}}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength) • Slew disabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$ • Slew enabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$	 — — — —	 12 6 36 24	 ns ns ns ns	4
	Port rise and fall time (low drive strength) • Slew disabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$ • Slew enabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$	 — — — —	 12 6 36 24	 ns ns ns ns	5

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75pF load
5. 15pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 10. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

Table 12. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	25	
	• Serial Wire Debug	0	50	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	20	—	ns
	• Serial Wire Debug	10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 13. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	20	
	• Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns

Table continues on the next page...

Table 20. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1
	Swap Control execution time					
$t_{swapx01}$	• control code 0x01	—	200	—	µs	
$t_{swapx02}$	• control code 0x02	—	70	150	µs	
$t_{swapx04}$	• control code 0x04	—	70	150	µs	
$t_{swapx08}$	• control code 0x08	—	—	30	µs	
	Program Partition for EEPROM execution time					
$t_{pgmpart32k}$	• 32 KB FlexNVM	—	70	—	ms	
	Set FlexRAM Function execution time:					
$t_{setramff}$	• Control Code 0xFF	—	50	—	µs	
$t_{setram8k}$	• 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{setram32k}$	• 32 KB EEPROM backup	—	0.7	1.0	ms	
	Byte-write to FlexRAM for EEPROM operation					
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	µs	3
	Byte-write to FlexRAM execution time:					
$t_{eewr8b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr8b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr8b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Word-write to FlexRAM for EEPROM operation					
$t_{eewr16bers}$	Word-write to erased FlexRAM location execution time	—	175	260	µs	
	Word-write to FlexRAM execution time:					
$t_{eewr16b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr16b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr16b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Longword-write to FlexRAM for EEPROM operation					
$t_{eewr32bers}$	Longword-write to erased FlexRAM location execution time	—	360	540	µs	
	Longword-write to FlexRAM execution time:					
$t_{eewr32b8k}$	• 8 KB EEPROM backup	—	545	1950	µs	
$t_{eewr32b16k}$	• 16 KB EEPROM backup	—	630	2050	µs	
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	810	2250	µs	

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

Table 28. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}-0.6V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

6.6.3.2 12-bit DAC operating behaviors

Table 30. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	150	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	700	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance load = 3 kΩ	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

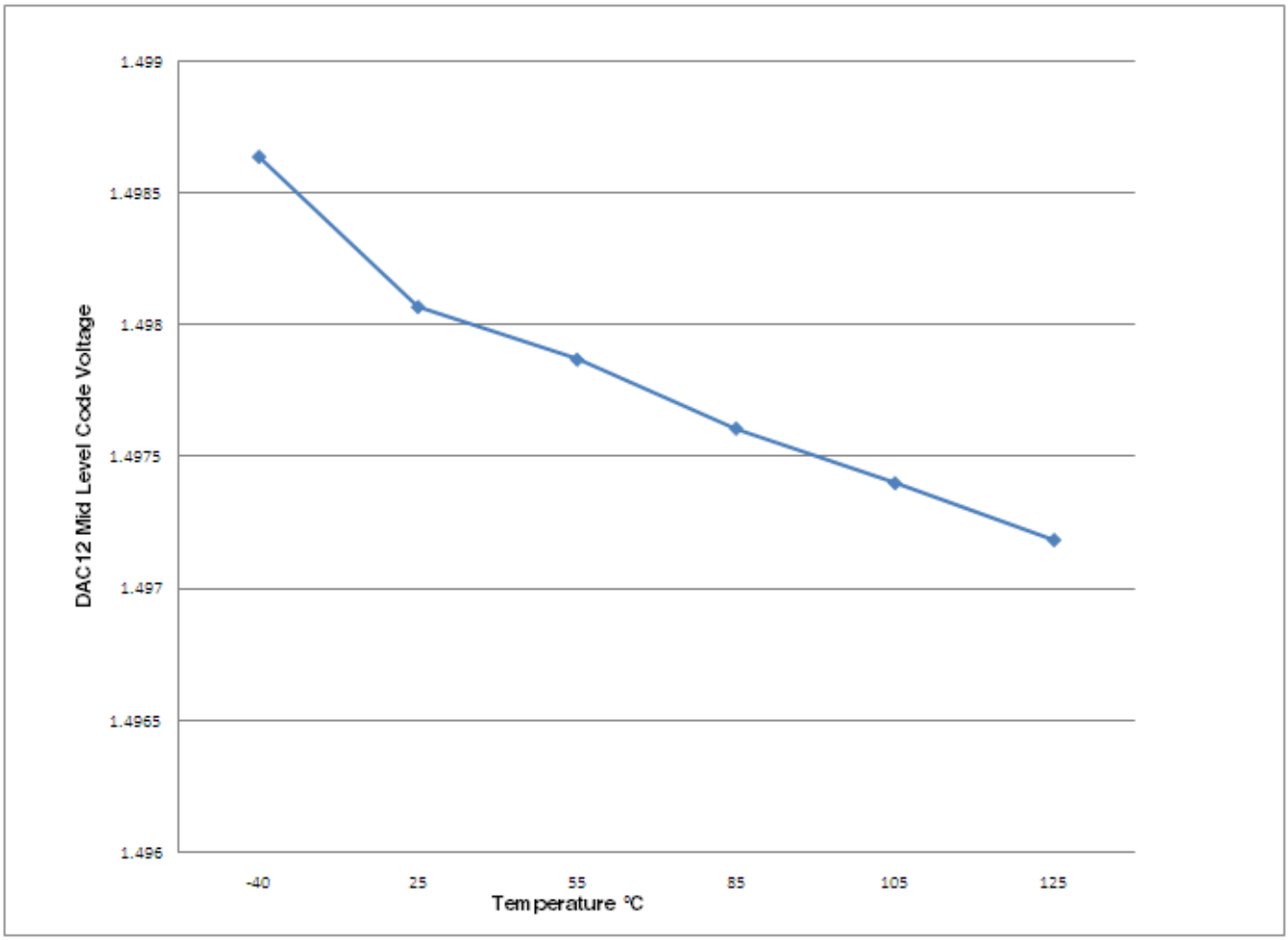


Figure 18. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 31. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

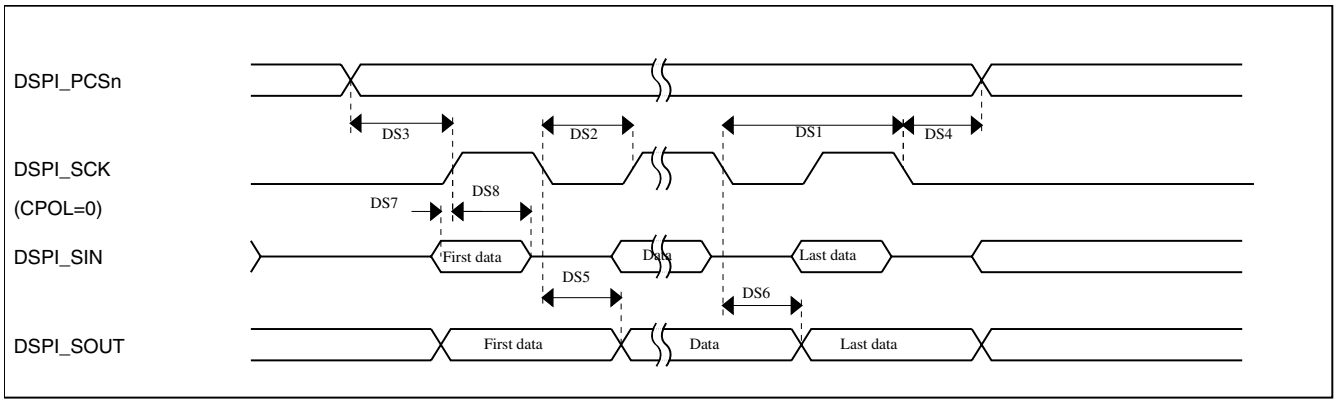


Figure 19. DSPI classic SPI timing — master mode

Table 38. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz
DS9	DSPI_SCK input cycle time	4 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) – 2	(t_{SCK}/2) + 2	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	10	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	14	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	14	ns

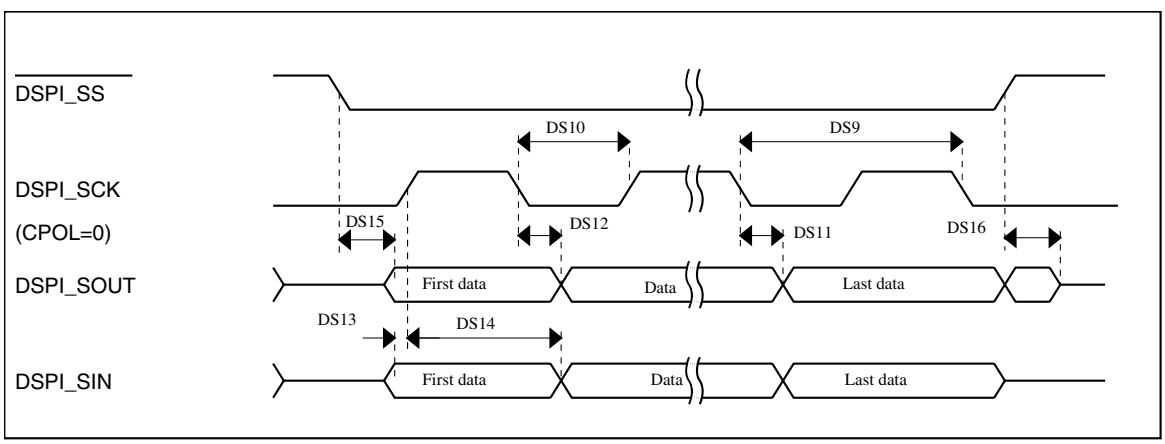


Figure 20. DSPI classic SPI timing — slave mode

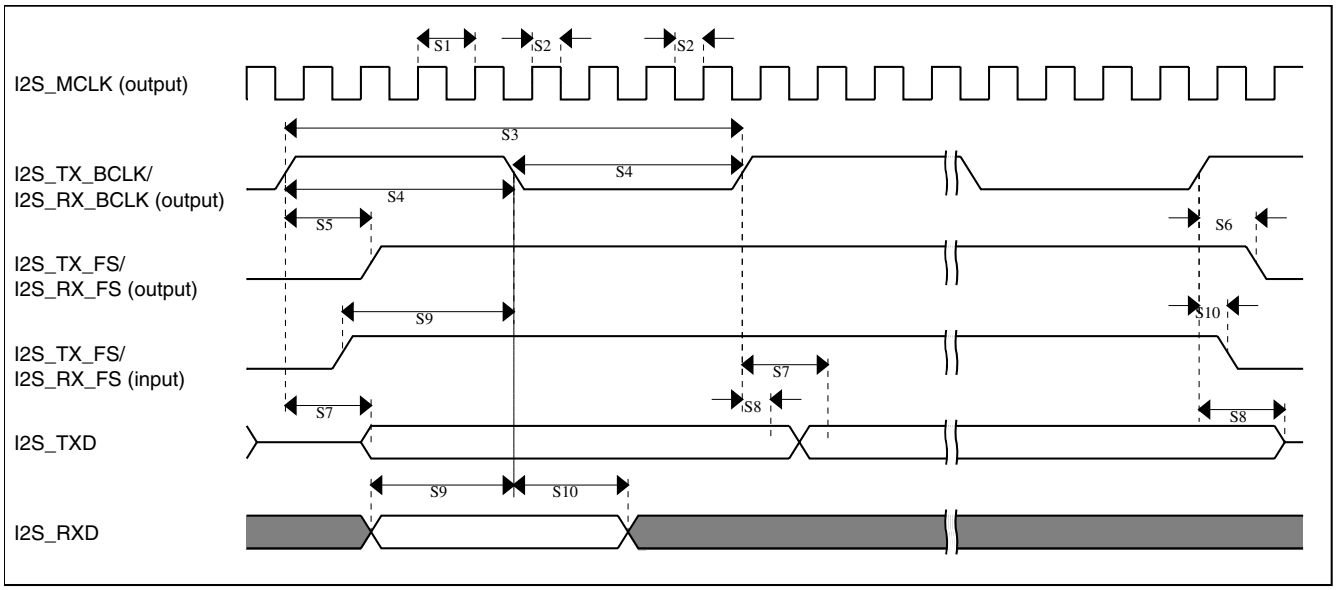


Figure 25. I2S/SAI timing — master modes

Table 44. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	7.6	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	67	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	6.5	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. Fixed external capacitance of 20 pF.
3. REFCHRG = 2, EXTCHRG=0.
4. REFCHRG = 0, EXTCHRG = 10.
5. V_{DD} = 3.0 V.
6. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
7. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
8. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; Iext = 16.
9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; Iext = 16.
10. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; Iext = 16.
11. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes. Sensitivity depends on the configuration used. The documented values are provided as examples calculated for a specific configuration of operating conditions using the following equation: (C_{ref} * I_{ext})/(I_{ref} * PS * NSCN)

    The typical value is calculated with the following configuration:

    I_{ext} = 6 µA (EXTCHRG = 2), PS = 128, NSCN = 2, I_{ref} = 16 µA (REFCHRG = 7), C_{ref} = 1.0 pF

    The minimum value is calculated with the following configuration:

    I_{ext} = 2 µA (EXTCHRG = 0), PS = 128, NSCN = 32, I_{ref} = 32 µA (REFCHRG = 15), C_{ref} = 0.5 pF

    The highest possible sensitivity is the minimum value because it represents the smallest possible capacitance that can be measured by a single count.
12. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, EXTCHRG = 7.
13. REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to www.freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
64-pin LQFP	98ASS23234W

8 Pinout

64 LQFP _QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
24	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSI0_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
25	PTA3	JTAG_TMS/ SWD_DIO	TSI0_CH4	PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
26	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSI0_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
27	PTA5	DISABLED		PTA5	USB_CLKIN	FTM0_CH2		CMP2_OUT	I2S0_TX_BCLK	JTAG_TRST_b	
28	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD0	FTM1_QD_ PHA	
29	PTA13/ LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_ PHB	
30	VDD	VDD	VDD								
31	VSS	VSS	VSS								
32	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
33	PTA19	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ALT1		
34	RESET_b	RESET_b	RESET_b								
35	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8/ TSI0_CH0	ADC0_SE8/ ADC1_SE8/ TSI0_CH0	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA		
36	PTB1	ADC0_SE9/ ADC1_SE9/ TSI0_CH6	ADC0_SE9/ ADC1_SE9/ TSI0_CH6	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_ PHB		
37	PTB2	ADC0_SE12/ TSI0_CH7	ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	UART0_RTS_b			FTM0_FLT3		
38	PTB3	ADC0_SE13/ TSI0_CH8	ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	UART0_CTS_ b/ UART0_COL_b			FTM0_FLT0		
39	PTB16	TSI0_CH9	TSI0_CH9	PTB16		UART0_RX		FB_AD17	EWM_IN		
40	PTB17	TSI0_CH10	TSI0_CH10	PTB17		UART0_TX		FB_AD16	EWM_OUT_b		
41	PTB18	TSI0_CH11	TSI0_CH11	PTB18	CAN0_TX	FTM2_CH0	I2S0_TX_BCLK	FB_AD15	FTM2_QD_ PHA		
42	PTB19	TSI0_CH12	TSI0_CH12	PTB19	CAN0_RX	FTM2_CH1	I2S0_TX_FS	FB_OE_b	FTM2_QD_ PHB		
43	PTC0	ADC0_SE14/ TSI0_CH13	ADC0_SE14/ TSI0_CH13	PTC0	SPI0_PCS4	PDB0_EXTRG		FB_AD14	I2S0_TXD1		
44	PTC1/ LLWU_P6	ADC0_SE15/ TSI0_CH14	ADC0_SE15/ TSI0_CH14	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0	FB_AD13	I2S0_TXD0		
45	PTC2	ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	ADC0_SE4b/ CMP1_IN0/ TSI0_CH15	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1	FB_AD12	I2S0_TX_FS		
46	PTC3/ LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT	I2S0_TX_BCLK		
47	VSS	VSS	VSS								
48	VDD	VDD	VDD								

64 LQFP _QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
49	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3	FB_AD11	CMP1_OUT		
50	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0	FB_AD10	CMP0_OUT		
51	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_EXTRG	I2S0_RX_BCLK	FB_AD9	I2S0_MCLK		
52	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN	USB_SOF_ OUT	I2S0_RX_FS	FB_AD8			
53	PTC8	ADC1_SE4b/ CMP0_IN2	ADC1_SE4b/ CMP0_IN2	PTC8			I2S0_MCLK	FB_AD7			
54	PTC9	ADC1_SE5b/ CMP0_IN3	ADC1_SE5b/ CMP0_IN3	PTC9			I2S0_RX_BCLK	FB_AD6	FTM2_FLT0		
55	PTC10	ADC1_SE6b	ADC1_SE6b	PTC10	I2C1_SCL		I2S0_RX_FS	FB_AD5			
56	PTC11/ LLWU_P11	ADC1_SE7b	ADC1_SE7b	PTC11/ LLWU_P11	I2C1_SDA		I2S0_RXD1	FB_RW_b			
57	PTD0/ LLWU_P12	DISABLED		PTD0/ LLWU_P12	SPI0_PCS0	UART2_RTS_b		FB_ALE/ FB_CS1_b/ FB_TS_b			
58	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b		FB_CS0_b			
59	PTD2/ LLWU_P13	DISABLED		PTD2/ LLWU_P13	SPI0_SOUT	UART2_RX		FB_AD4			
60	PTD3	DISABLED		PTD3	SPI0_SIN	UART2_TX		FB_AD3			
61	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4	FB_AD2	EWM_IN		
62	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_ b/ UART0_COL_b	FTM0_CH5	FB_AD1	EWM_OUT_b		
63	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6	FB_AD0	FTM0_FLT0		
64	PTD7	DISABLED		PTD7	CMT_IRO	UART0_TX	FTM0_CH7		FTM0_FLT1		

8.2 K20 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

Table 46. Revision History

Rev. No.	Date	Substantial Changes
1	3/2012	Initial public release
2	4/2012	• Replaced TBDs throughout. • Updated "Power consumption operating behaviors" table. • Updated "ADC electrical specifications" section. • Updated "VREF full-range operating behaviors" table. • Updated "I2S/SAI Switching Specifications" section. • Updated "TSI electrical specifications" table.
3	11/2012	• Updated orderable part numbers. • Updated the maximum input voltage (V_{ADIN}) specification in the "16-bit ADC operating conditions" section. • Updated the maximum I_{DDstby} specification in the "USB VREG electrical specifications" section.

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Document Number: K20P64M72SF1
Rev. 3, 11/2012